



**THE DATASHEET OF  
NTJD3158CT1G**



# NTJD3158C

## Power MOSFET

20 V, +0.63/-0.82 A,  
SC-88 Complementary, ESD Protected

### Features

- Complementary N- and P-Channel MOSFET
- Small Size Dual SC-88 Package
- Reduced Gate Charge to Improve Switching Response
- Independently Connected Devices to Provide Design Flexibility
- This is a Pb-Free Device

### Applications

- DC-DC Conversion Circuits
- Load/Power Switching with Level Shift

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V <sub>DSS</sub>	20	V	
Gate-to-Source Voltage		V <sub>GS</sub>	±12	V	
<b>N-Channel</b> Continuous Drain Current (Note 1)	Steady State	T <sub>A</sub> = 25°C	I <sub>D</sub>	0.63	A
		T <sub>A</sub> = 85°C		0.46	
	t ≤ 5 s	T <sub>A</sub> = 25°C		0.72	
<b>P-Channel</b> Continuous Drain Current (Note 1)	Steady State	T <sub>A</sub> = 25°C	I <sub>D</sub>	-0.82	A
		T <sub>A</sub> = 85°C		-0.59	
	t ≤ 5 s	T <sub>A</sub> = 25°C		-0.93	
Power Dissipation (Note 1)	Steady State	T <sub>A</sub> = 25°C	P <sub>D</sub>	0.27	W
	t ≤ 5 s			0.35	
Pulsed Drain Current	N-Ch	tp = 10 μs	I <sub>DM</sub>	1.3	A
	P-Ch			-1.6	
Operating Junction and Storage Temperature		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C	
Source Current (Body Diode)		I <sub>S</sub>	0.46	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T <sub>L</sub>	260	°C	

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	R <sub>θJA</sub>	460	°C/W
Junction-to-Ambient – t ≤ 5 s (Note 1)	R <sub>θJA</sub>	357	
Junction-to-Lead (Drain) – Steady State (Note 1)	R <sub>θJL</sub>	226	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

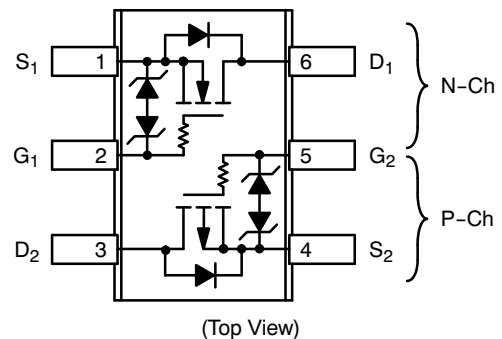


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V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> Max	I <sub>D</sub> Max
N-Ch 20 V	375 mΩ @ 4.5 V	0.63 A
	445 mΩ @ 2.5 V	
P-Ch -20 V	300 mΩ @ -4.5 V	-0.82 A
	500 mΩ @ -2.5 V	

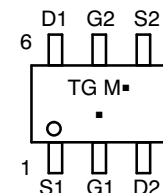
### SC-88 (SOT-363) (6-Leads)



### MARKING DIAGRAM & PIN ASSIGNMENT



SC-88 (SOT-363)  
CASE 419B  
STYLE 26



- TG = Specific Device Code
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
NTJD3158CT1G	SC-88 (Pb-Free)	3000/Tape & Reel
NTJD3158CT4G	SC-88 (Pb-Free)	10000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NTJD3158C

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	N/P	Test Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS (Note 3)</b>							
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	N	V <sub>GS</sub> = 0 V	I <sub>D</sub> = 250 μA	20		V
		P		I <sub>D</sub> = -250 μA	-20		
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>				22		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	N	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 16 V			1.0	μA
		P	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = -16 V			1.0	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	N	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±12 V			±10	μA
		P	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±4.5 V			±1.0	
		P	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±12 V		6.0		

## ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V <sub>GS(TH)</sub>	N	I <sub>D</sub> = 250 μA	0.6		1.5	V
		P	I <sub>D</sub> = -250 μA	-0.45			
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	N	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 0.63 A		290	375	mΩ
		P	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -0.88 A		255	300	
		N	V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 0.40 A		360	445	
		P	V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -0.71 A		345	500	
Forward Transconductance	g <sub>FS</sub>	N	V <sub>DS</sub> = 4.0 V, I <sub>D</sub> = 0.63 A		2.0		S
		P	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -0.88 A		3.0		

## CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C <sub>ISS</sub>	N	f = 1 MHz, V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 20 V		33	46	pF	
		P		V <sub>DS</sub> = -20 V		155			
Output Capacitance	C <sub>OSS</sub>	N		V <sub>DS</sub> = 20 V		13	22		
		P		V <sub>DS</sub> = -20 V		25			
Reverse Transfer Capacitance	C <sub>RSS</sub>	N		V <sub>DS</sub> = 20 V		2.8	5.0		
		P		V <sub>DS</sub> = -20 V		18			
Total Gate Charge	Q <sub>G(TOT)</sub>	N		V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.63 A		1.3	3.0		nC
		P		V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -15 V, I <sub>D</sub> = -0.88 A		2.2			
Gate-to-Source Charge	Q <sub>GS</sub>	N	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.63 A		0.2				
		P	V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -15 V, I <sub>D</sub> = -0.88 A		0.5				
Gate-to-Drain Charge	Q <sub>GD</sub>	N	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.63 A		0.4				
		P	V <sub>GS</sub> = -4.5 V, V <sub>DS</sub> = -10 V, I <sub>D</sub> = -0.88 A		0.65				

## SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t <sub>d(ON)</sub>	N	V <sub>GS</sub> = 4.5 V, V <sub>DD</sub> = 10 V, I <sub>D</sub> = 0.5 A, R <sub>G</sub> = 20 Ω		83		ns
Rise Time	t <sub>r</sub>				227		
Turn-Off Delay Time	t <sub>d(OFF)</sub>				786		
Fall Time	t <sub>f</sub>				506		
Turn-On Delay Time	t <sub>d(ON)</sub>	P	V <sub>GS</sub> = -4.5 V, V <sub>DD</sub> = -10 V, I <sub>D</sub> = -0.5 A, R <sub>G</sub> = 20 Ω		5.8		
Rise Time	t <sub>r</sub>				6.5		
Turn-Off Delay Time	t <sub>d(OFF)</sub>				13.5		
Fall Time	t <sub>f</sub>				3.5		

## DRAIN-SOURCE DIODE CHARACTERISTICS

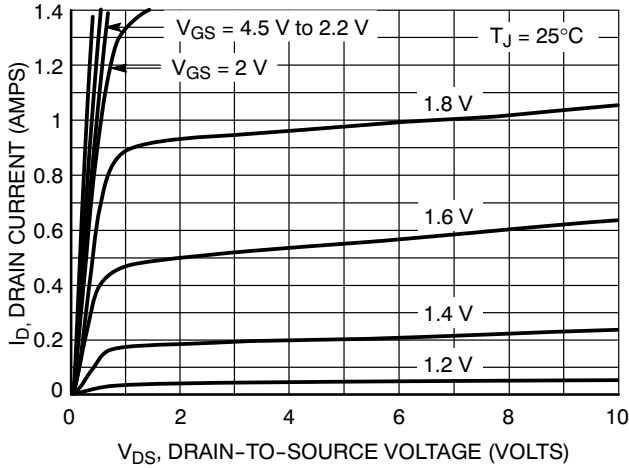
Forward Diode Voltage	V <sub>SD</sub>	N	V <sub>GS</sub> = 0 V, T <sub>J</sub> = 25°C	I <sub>S</sub> = 0.23 A	0.76	1.1	V
		P		I <sub>S</sub> = -0.48 A	-0.8	-1.2	
		N	V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125°C	I <sub>S</sub> = 0.23 A	0.63		
		P		I <sub>S</sub> = -0.48 A	-0.66		

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

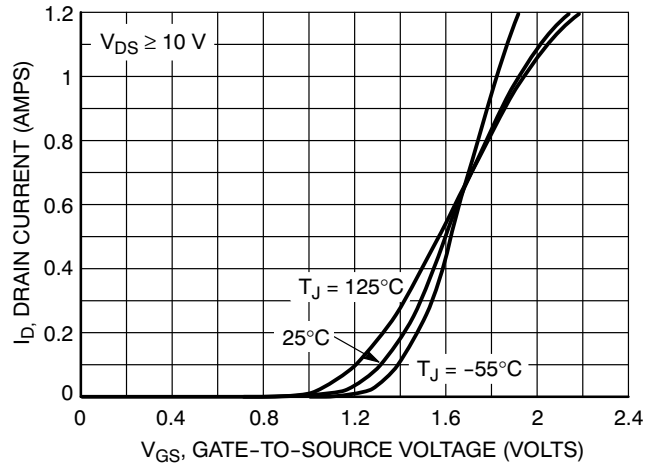
3. Switching characteristics are independent of operating junction temperatures.

# NTJD3158C

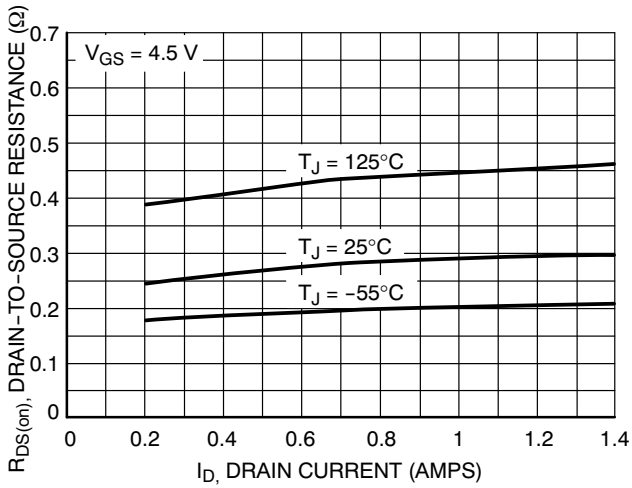
## TYPICAL PERFORMANCE CURVES (N-Ch) ( $T_J = 25^\circ\text{C}$ unless otherwise noted)



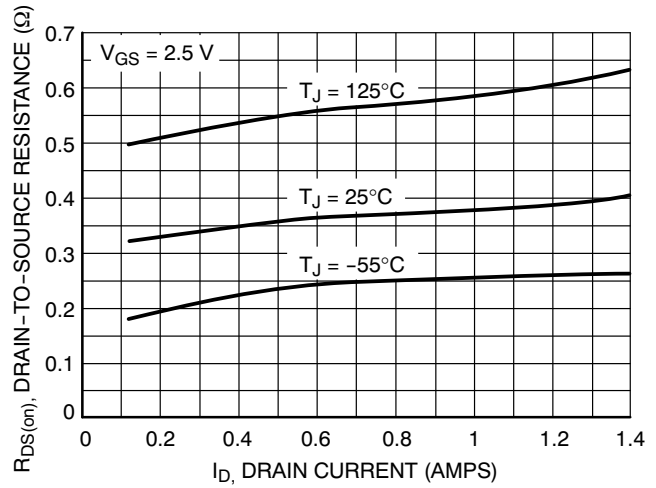
**Figure 1. On-Region Characteristics**



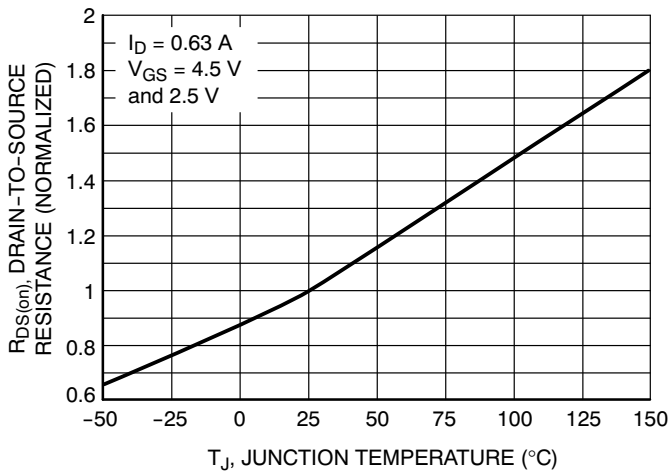
**Figure 2. Transfer Characteristics**



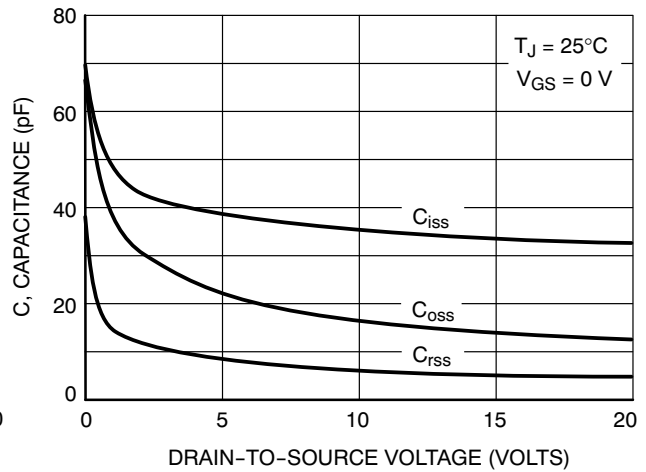
**Figure 3. On-Resistance vs. Drain Current and Temperature**



**Figure 4. On-Resistance vs. Drain Current and Temperature**



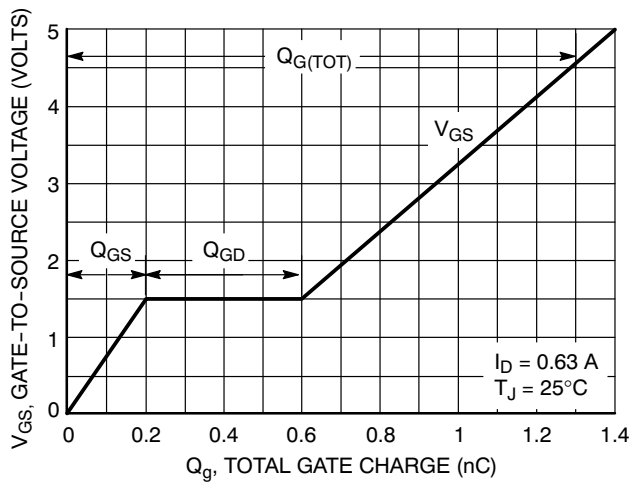
**Figure 5. On-Resistance Variation with Temperature**



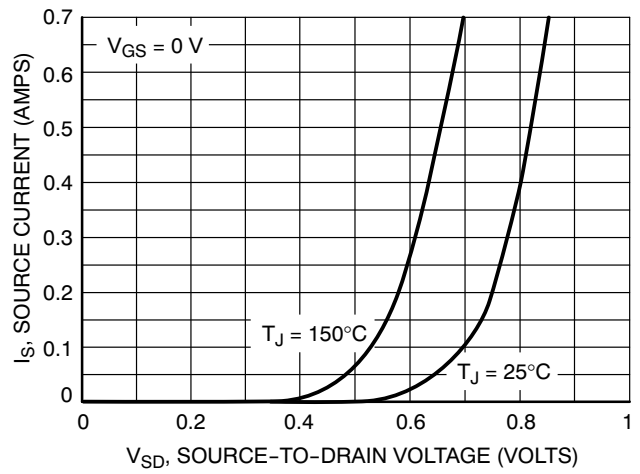
**Figure 6. Capacitance Variation**

# NTJD3158C

## TYPICAL PERFORMANCE CURVES (N-Ch) ( $T_J = 25^\circ\text{C}$ unless otherwise noted)



**Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge**



**Figure 8. Diode Forward Voltage vs. Current**

TYPICAL PERFORMANCE CURVES (P-Ch) ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

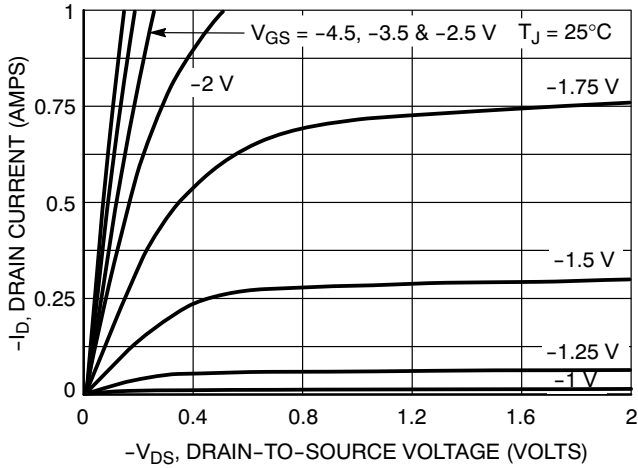


Figure 9. On-Region Characteristics

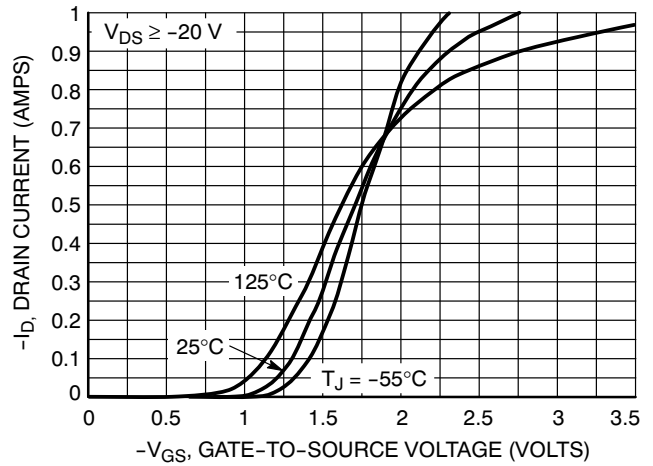


Figure 10. Transfer Characteristics

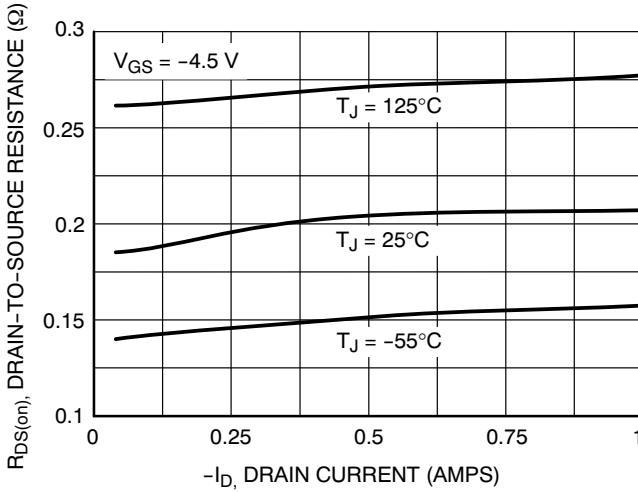


Figure 11. On-Resistance vs. Drain Current and Temperature

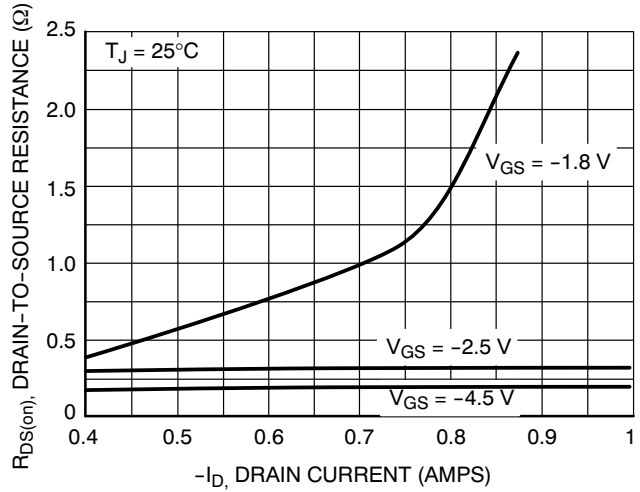


Figure 12. On-Resistance vs. Drain Current and Gate Voltage

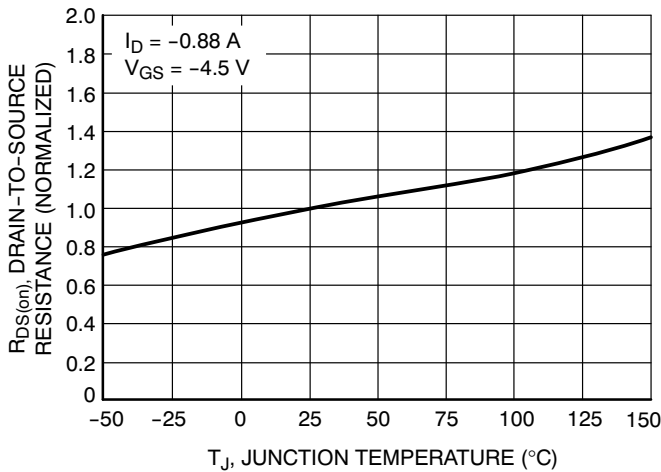


Figure 13. On-Resistance Variation with Temperature

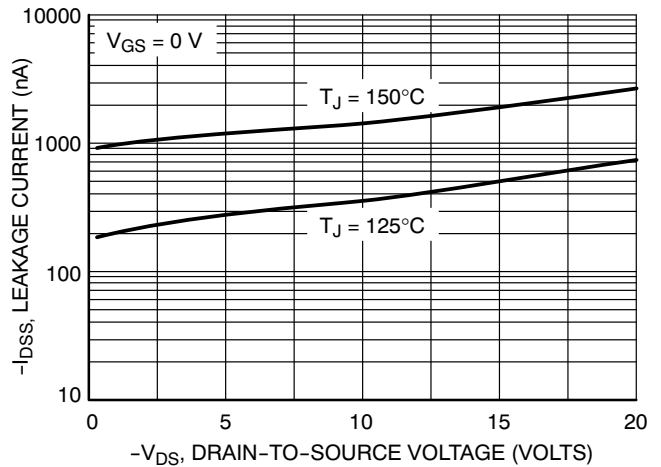


Figure 14. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES (P-Ch) ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

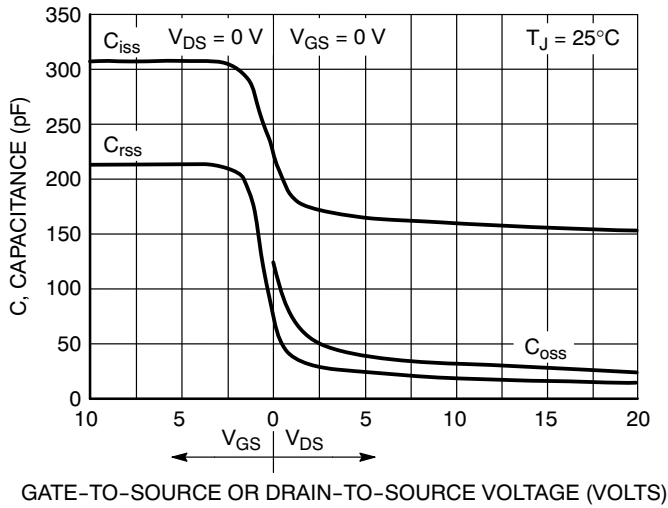


Figure 15. Capacitance Variation

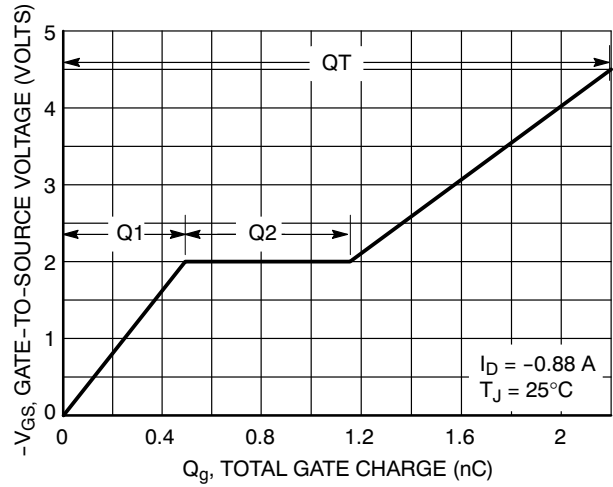


Figure 16. Gate-to-Source Voltage vs. Total Gate Charge

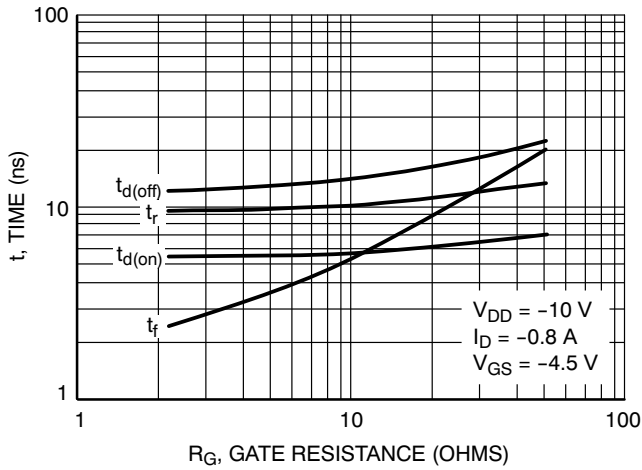


Figure 17. Resistive Switching Time Variation vs. Gate Resistance

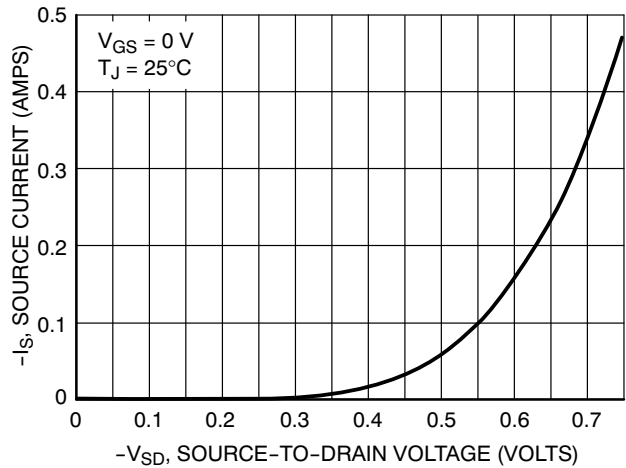


Figure 18. Diode Forward Voltage vs. Current

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

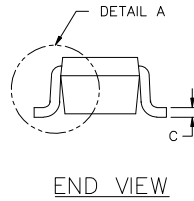
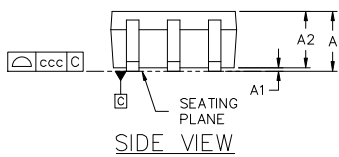
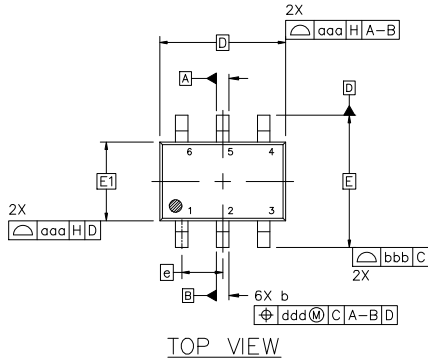


**SC-88 2.00x1.25x0.90, 0.65P**  
CASE 419B-02  
ISSUE Z

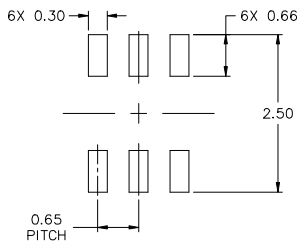
DATE 18 APR 2024

NOTES:

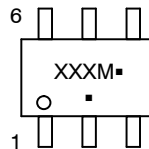
1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.00	---	0.10
A2	0.70	0.90	1.00
b	0.15	0.20	0.25
c	0.08	0.15	0.22
D	2.00 BSC		
E	2.10 BSC		
E1	1.25 BSC		
e	0.65 BSC		
L	0.26	0.36	0.46
L2	0.15 BSC		
aaa	0.15		
bbb	0.30		
ccc	0.10		
ddd	0.10		



**GENERIC MARKING DIAGRAM\***



- XXX = Specific Device Code
- M = Date Code\*
- = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

**STYLES ON PAGE 2**

\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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<b>DESCRIPTION:</b>	<b>SC-88 2.00x1.25x0.90, 0.65P</b>	<b>PAGE 1 OF 2</b>

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**SC-88 2.00x1.25x0.90, 0.65P**  
**CASE 419B-02**  
**ISSUE Z**

DATE 18 APR 2024

<b>STYLE 1:</b> PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	<b>STYLE 2:</b> CANCELLED	<b>STYLE 3:</b> CANCELLED	<b>STYLE 4:</b> PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	<b>STYLE 5:</b> PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	<b>STYLE 6:</b> PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
<b>STYLE 7:</b> PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	<b>STYLE 8:</b> CANCELLED	<b>STYLE 9:</b> PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	<b>STYLE 10:</b> PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	<b>STYLE 11:</b> PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	<b>STYLE 12:</b> PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
<b>STYLE 13:</b> PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	<b>STYLE 14:</b> PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	<b>STYLE 15:</b> PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	<b>STYLE 16:</b> PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	<b>STYLE 17:</b> PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	<b>STYLE 18:</b> PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
<b>STYLE 19:</b> PIN 1. IOUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	<b>STYLE 20:</b> PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	<b>STYLE 21:</b> PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	<b>STYLE 22:</b> PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	<b>STYLE 23:</b> PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	<b>STYLE 24:</b> PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
<b>STYLE 25:</b> PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	<b>STYLE 26:</b> PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	<b>STYLE 27:</b> PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	<b>STYLE 28:</b> PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	<b>STYLE 29:</b> PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	<b>STYLE 30:</b> PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

<b>DOCUMENT NUMBER:</b>	<b>98ASB42985B</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>SC-88 2.00x1.25x0.90, 0.65P</b>	<b>PAGE 2 OF 2</b>

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